SGS-THOMSON MICROELECTRONICS

M74HC154

4 TO 16 LINE DECODER/DEMULTIPLEXER

- HIGH SPEED
- t_{PD} = 15 ns (TYP.) at V_{CC} = 5 V
- LOW POWER DISSIPATION
  I_{CC} = 4 μA (MAX.) at T_A = 25 °C
- HIGH NOISE IMMUNITY
  V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  15 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|IOH|$ = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  t_{PLH} = t_{PHL}
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2 V to 6 V
- PIN AND FUNCTION COMPATIBLE
  WITH 54/74LS154

B1R
(Plastic Package)

M1R
(Micro Package)

ORDER CODES :
M74HC154B1R   M74HC154M1R

DESCRIPTION

The 74HC154 is a high speed CMOS 4 TO 16-LINE DECODER/DEMULTIPLEXER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

A binary code applied to the four inputs (A to D) provides a low level at the selected one of sixteen outputs excluding the other fifteen outputs, when both the strobe inputs, G1 and G2, are held low. When either strobe input is held high, the decoding function is inhibited to keep all outputs high. The strobe function makes it easy to expand the decoding lines through cascading, and simplifies the design of address decoding circuits in memory control systems.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTIONS (top view)

|		
$\overline{Y0}$	1	24	V_{CC}
$\overline{Y1}$	2	23	A
$\overline{Y2}$	3	22	B
$\overline{Y3}$	4	21	C
$\overline{Y4}$	5	20	D
$\overline{Y5}$	6	19	$\overline{G2}$
$\overline{Y6}$	7	18	$\overline{G1}$
$\overline{Y7}$	8	17	$\overline{Y15}$
$\overline{Y8}$	9	16	$\overline{Y14}$
$\overline{Y9}$	10	15	$\overline{Y13}$
$\overline{Y10}$	11	14	$\overline{Y12}$
GND	12	13	$\overline{Y11}$

S-7412

NC =
No Internal
Connection
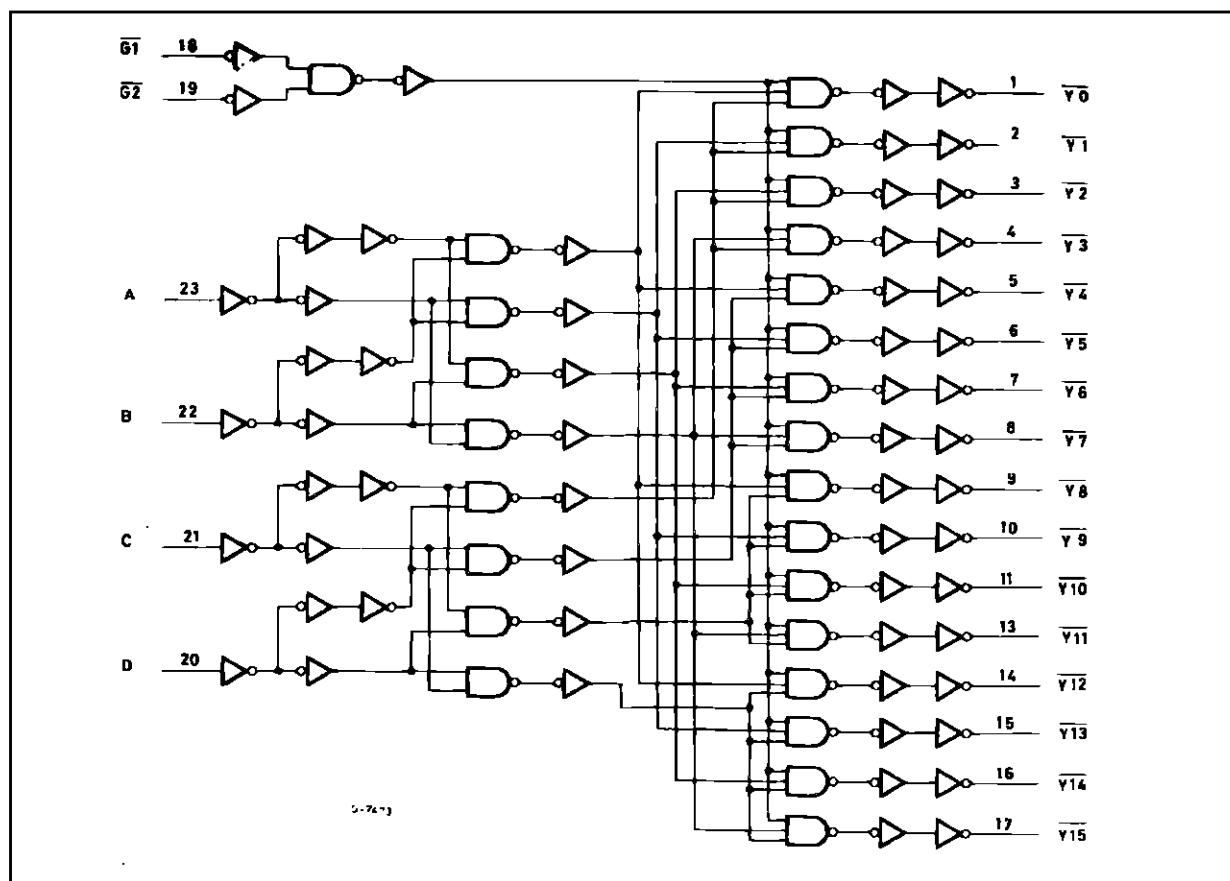
TRUTH TABLE
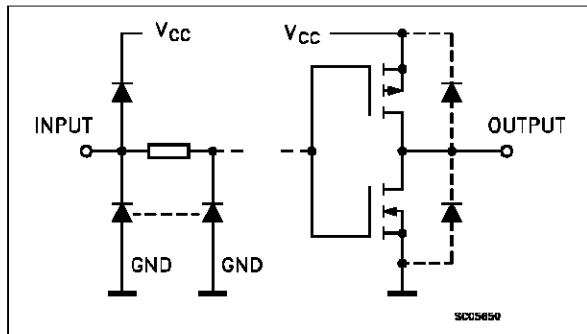
INPUTS						SELECTED OUTPUT (L)
$\overline{G1}$	$\overline{G2}$	D	C	B	A	
L	L	L	L	L	L	$\overline{Y0}$
L	L	L	L	L	H	$\overline{Y1}$
L	L	L	L	H	L	$\overline{Y2}$
L	L	L	L	H	H	$\overline{Y3}$
L	L	L	H	L	L	$\overline{Y4}$
L	L	L	H	L	H	$\overline{Y5}$
L	L	L	H	H	L	$\overline{Y6}$
L	L	L	H	H	H	$\overline{Y7}$
L	L	H	L	L	L	$\overline{Y8}$
L	L	H	L	L	H	$\overline{Y9}$
L	L	H	L	H	L	$\overline{Y10}$
L	L	H	L	H	H	$\overline{Y11}$
L	L	H	H	L	L	$\overline{Y12}$
L	L	H	H	L	H	$\overline{Y13}$
L	L	H	H	H	L	$\overline{Y14}$
L	L	H	H	H	H	$\overline{Y15}$
X	H	X	X	X	X	NONE
H	X	X	X	X	X	NONE

X: Don't Care

LOGIC DIAGRAM

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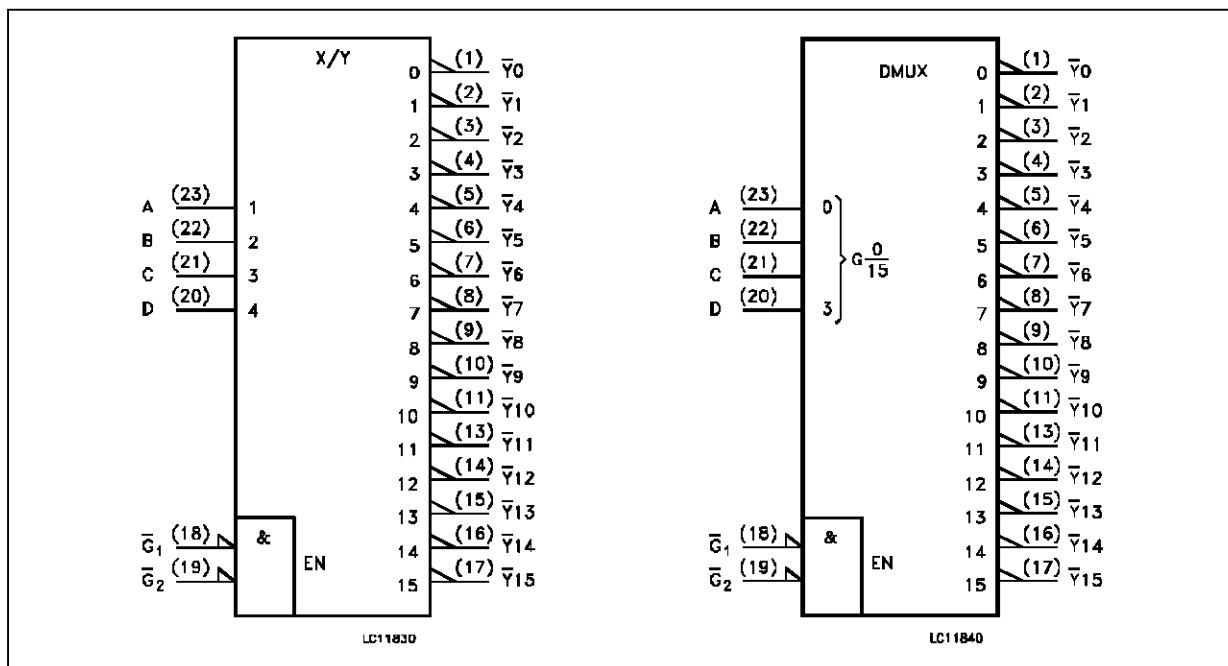
INPUT AND OUTPUT EQUIVALENT CIRCUIT

PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11, 13, 14, 15, 16, 17	$\overline{Y0}$ to $\overline{Y15}$	Outputs (Active LOW)
18, 19	$\overline{G1}$, $\overline{G2}$	Enable Inputs (Active LOW)
23, 22, 21, 20	A to D	Address Inputs
12	GND	Ground (0V)
24	V_{CC}	Positive Supply Voltage

IEC LOGIC SYMBOLS

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	^{o}C
T_L	Lead Temperature (10 sec)	300	^{o}C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
(*) 500 mW: $\cong$ 65 ^{o}C derate to 300 mW by 10mW/^{o}C: 65 ^{o}C to 85 ^{o}C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature:		-40 to +85	^{o}C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS
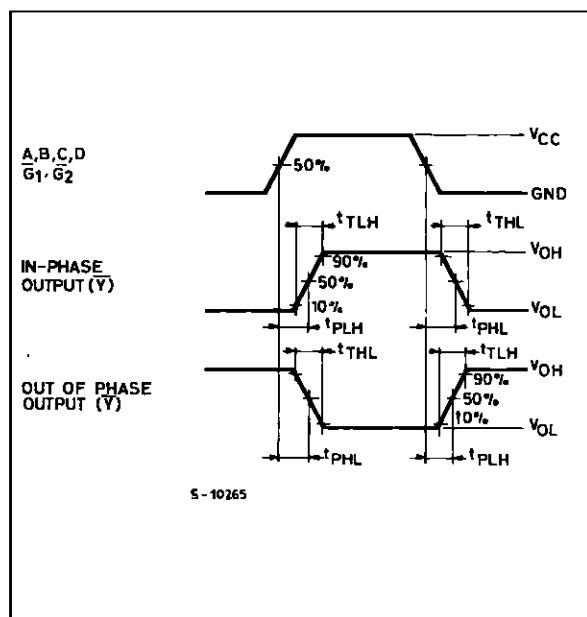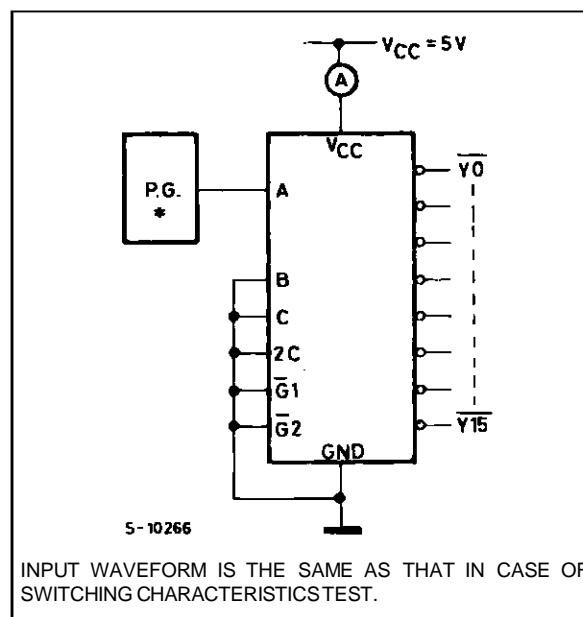
Symbol	Parameter	Test Conditions		Value					Unit
		V_{CC} (V)		T_A = 25 ^{o}C			-40 to 85 ^{o}C		
				Min.	Typ.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0		1.5			1.5		V
		4.5		3.15			3.15		
		6.0		4.2			4.2		
V_{IL}	Low Level Input Voltage	2.0				0.5		0.5	V
		4.5				1.35		1.35	
		6.0				1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		V
		4.5			4.4	4.5		4.4		
		6.0			5.9	6.0		5.9		
		4.5		I_O=-4.0 mA	4.18	4.31		4.13		
		6.0		I_O=-5.2 mA	5.68	5.8		5.63		
V_{OL}	Low Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1	V
		4.5				0.0	0.1		0.1	
		6.0				0.0	0.1		0.1	
		4.5		I_O= 4.0 mA		0.17	0.26		0.33	
		6.0		I_O= 5.2 mA		0.18	0.26		0.33	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND			±0.1		±1	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND			4		40	µA

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AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

Symbol	Parameter	Test Conditions		Value					Unit
		V_{CC} (V)		T_A = 25 ^{o}C			-40 to 85 ^{o}C		
				Min.	Typ.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0			30	75		95	ns
		4.5			8	15		19	
		6.0			7	13		16	
t_{PLH} t_{PHL}	Propagation Delay Time (A, B, C, D - $\overline{Y}$)	2.0			65	175		220	ns
		4.5			19	35		44	
		6.0			16	30		37	
t_{PLH} t_{PHL}	Propagation Delay Time ($\overline{G1}$, $\overline{G2}$ - Y)	2.0			55	160		200	ns
		4.5			17	32		40	
		6.0			15	27		34	
C_{IN}	Input Capacitance				5	10		10	pF
C_{PD} (*)	Power Dissipation Capacitance				57				pF
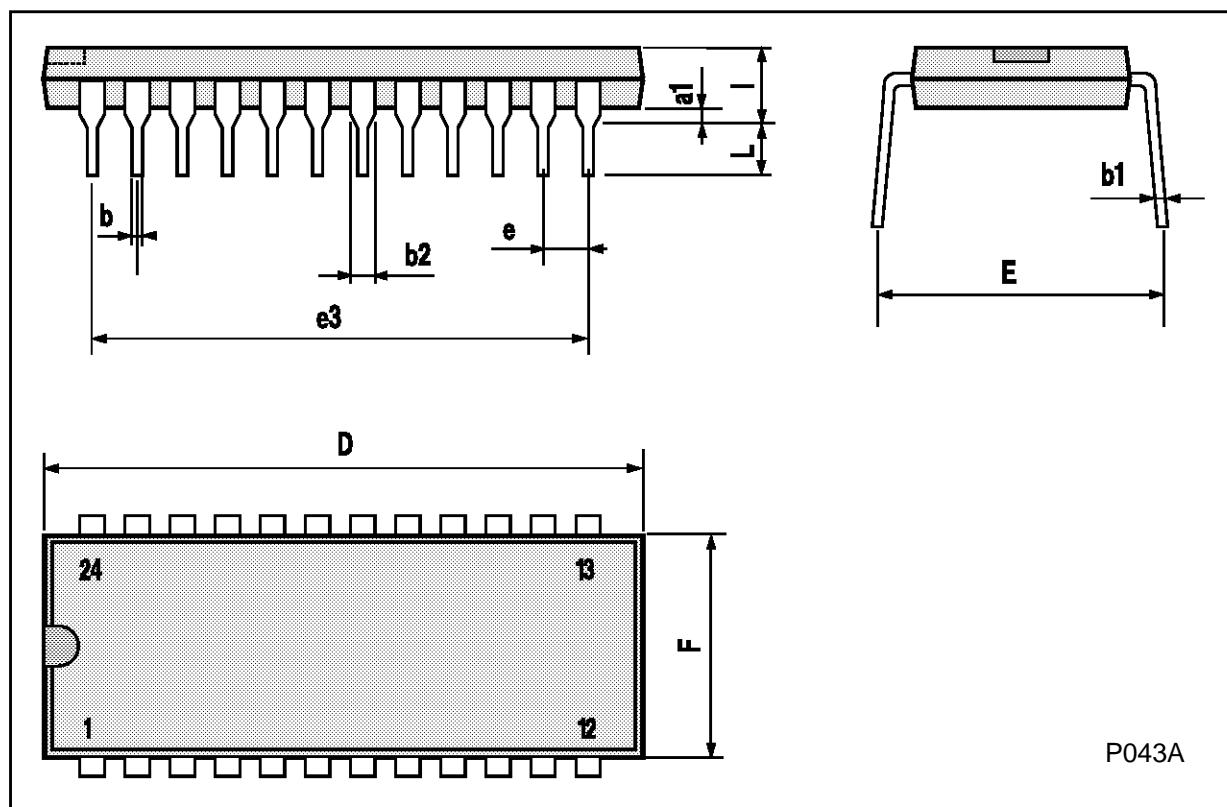
(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$

### SWITCHING CHARACTERISTICS TEST CIRCUIT

TEST CIRCUIT I_{CC} (Opr.)

INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

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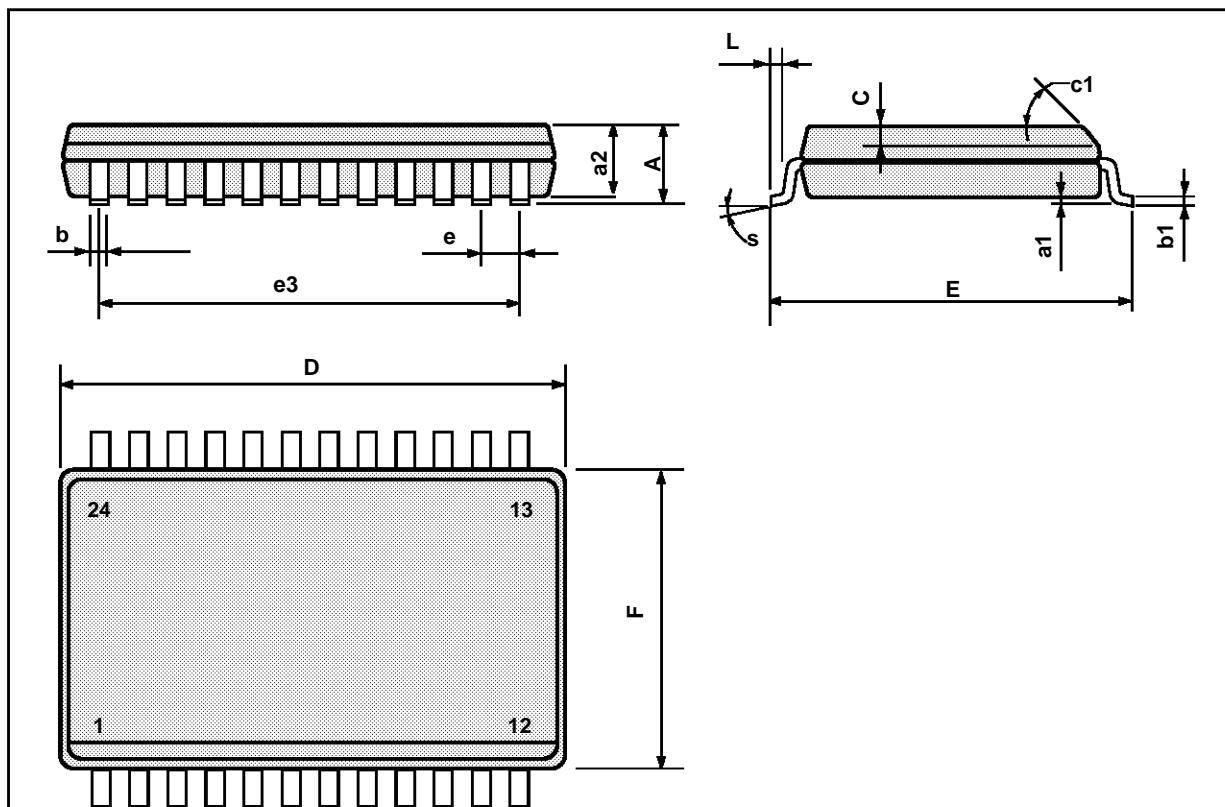
Plastic DIP24 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1		0.63			0.025	
b		0.45			0.018	
b1	0.23		0.31	0.009		0.012
b2		1.27			0.050	
D			32.2			1.268
E	15.2		16.68	0.598		0.657
e		2.54			0.100	
e3		27.94			1.100	
F			14.1			0.555
I		4.445			0.175	
L		3.3			0.130	

P043A

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SO24 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45° (typ.)					
D	15.20		15.60	0.598		0.614
E	10.00		10.65	0.393		0.420
e		1.27			0.05	
e3		13.97			0.55	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
S	8° (max.)					

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